TOSHIBA INSULATED GATE BIPOLAR TRANSISTOR SILICON N CHANNEL IGBT

GT10J303

HIGH POWER SWITCHING APPLICATIONS MOTOR CONTROL APPLICATIONS

Third-generation IGBT

Enhancement mode type

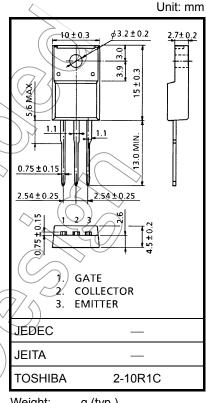
: $t_f = 0.30 \mu s \text{ (Max.) (IC} = 10 \text{A)}$ High speed

Low saturation voltage : V_{CE} (sat) = 2.7V (Max.) (IC = 10A)

FRD included between emitter and collector

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

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CHARACTERISTIC		SYMBOL	RATING	UNIT	
Collector-Emitter Voltage		V _{CES}	600	\\y	
Gate-Emitter Voltage		V _{GES}	±20	> V	
Collector Current	DC	IC		Α	
	1ms	ICP	20	Α	
Emitter-Collector Forward Current	DC	l _F	10	A	
	1ms	I _{FM}	20	<< A	
Collector Power Dissipation (Tc = 25°C)		PC	30	w	
Junction Temperature		(Tj <	150	\ °C	
Storage Temperature Range		T _{stg}	−55~150 °C		

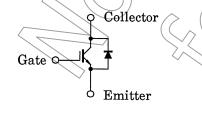


Weight: g (typ.)

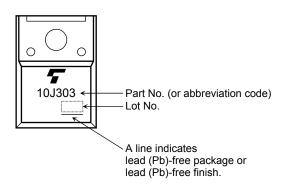
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature)current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

EQUIVALENT CIRCUIT



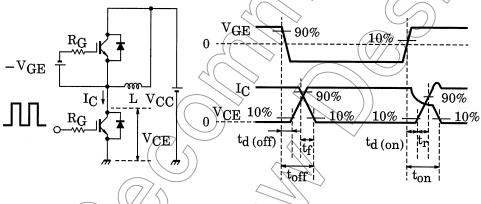
MARKING



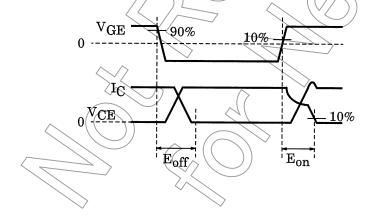
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARA	CTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT
Gate Leakage Curr	rent	I _{GES}	V _{GE} = ±20V, V _{CE} = 0	_	_	±500	nA
Collector Cut-Off C	Current	I _{CES}	V _{CE} = 600V, V _{GE} = 0	_	_	1.0	mA
Gate-Emitter Cut-0	Off Voltage	V _{GE} (OFF)	I _C = 1mA, V _{CE} = 5V	5.0	_	8.0	V
Collector-Emitter S	Saturation Voltage	V _{CE} (sat)	I _C = 10A, V _{GE} = 15V		2.1	2.7	V
Input Capacitance		C _{ies}	V _{CE} = 20V, V _{GE} = 0, f = 1MHz		720	_	pF
Switching Time Fall 1	Rise Time	t _r	Inductive Load	\nearrow	0.12	_	
	Turn-On Time	ton	V _{CC} = 300V, I _C = 10A))	0.40	_	
	Fall Time	t _f	$V_{GG} = \pm 15V$, $R_G = 100\Omega$ (Note 1)	_	0.15	0.30	μs
	Turn-Off Time	t _{off}		^ —	0.50	_	
Peak Forward Volta	age	V _F	I _F = 10A, V _{GE} = 0	_		2.0	V
Reverse Recovery	Time	t _{rr}	I _F = 10A, di / dt = -100A / μs		4	200	ns
Thermal Resistanc	e (IGBT)	R _{th (j-c)}		-	(-/	> 4.17	°C / W
Thermal Resistance	e (Diode)	R _{th (j-c)}			2)/5	4.9	°C / W

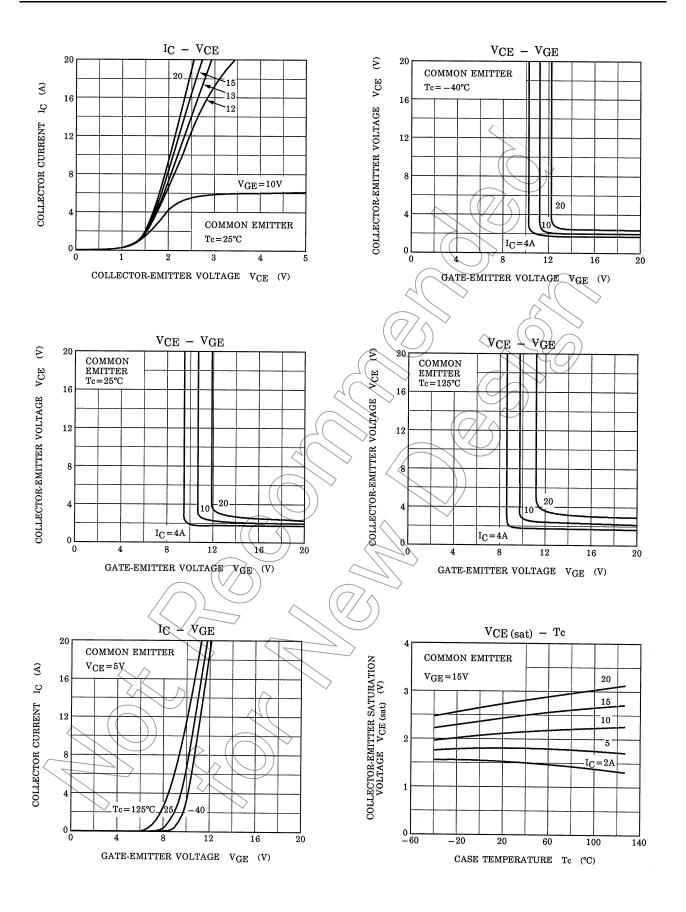
Note 1: Switching time measurement circuit and input / output waveforms

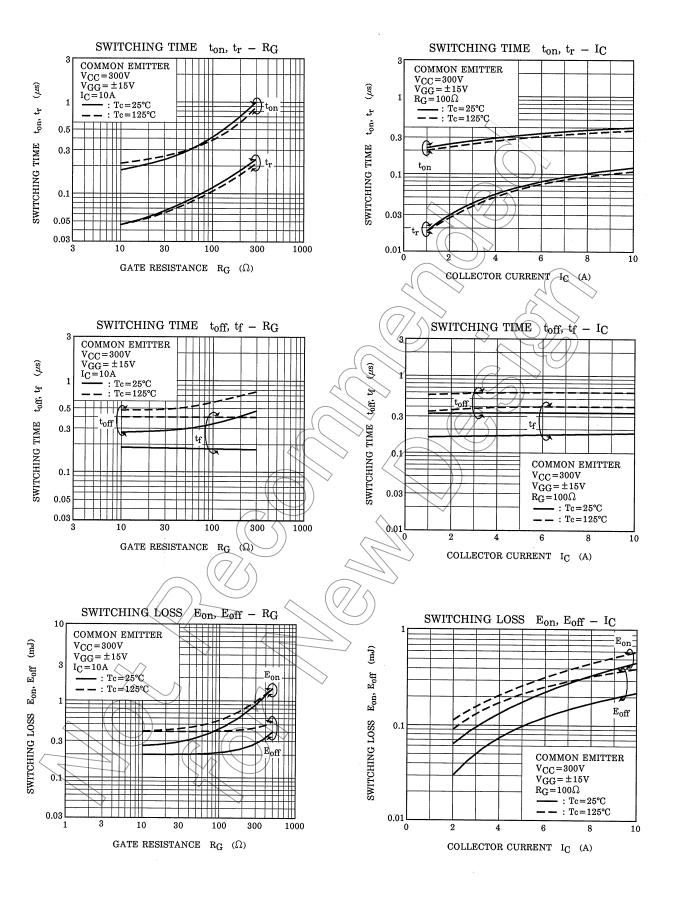


Switching loss measurement waveforms

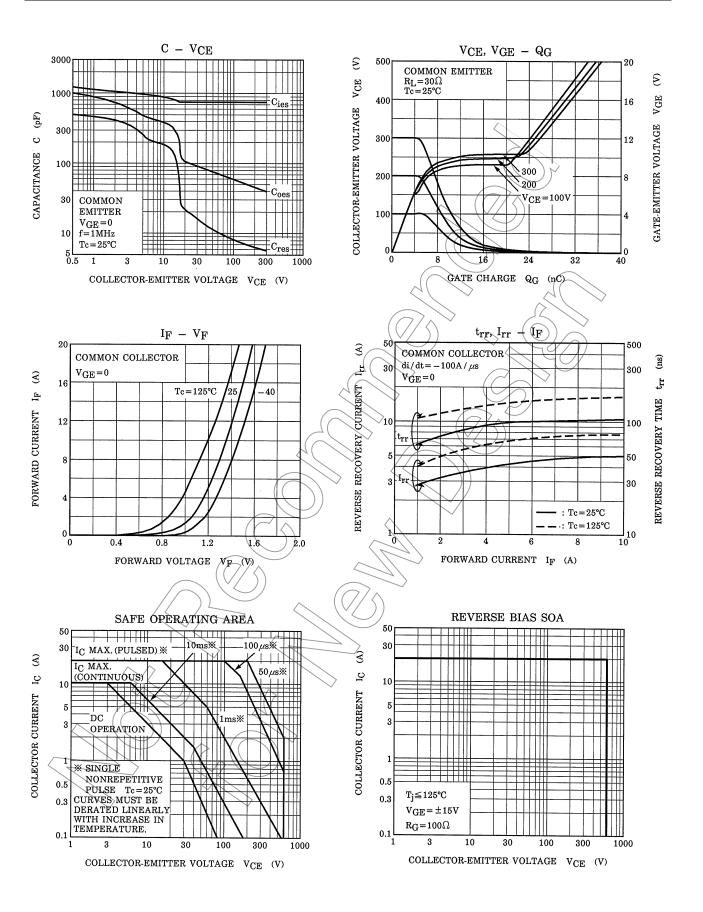


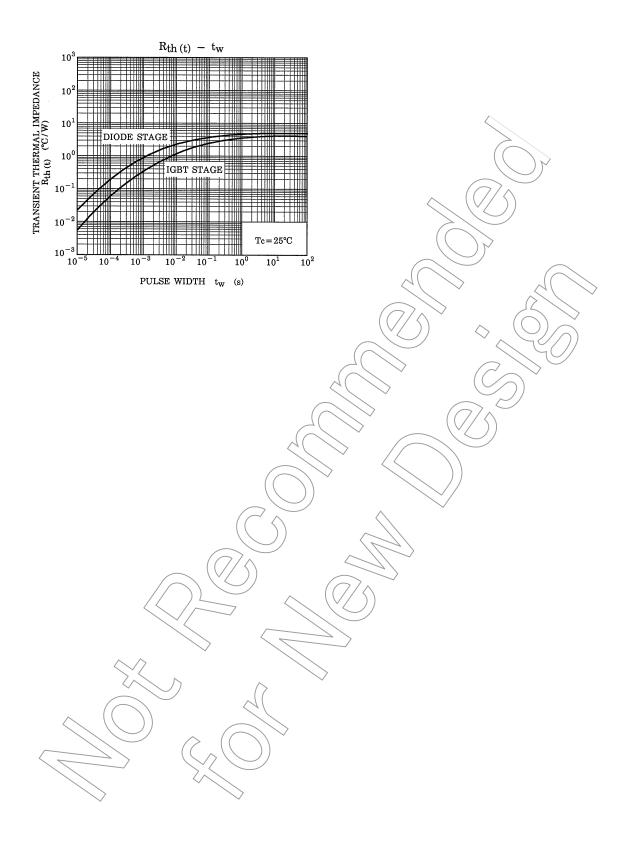
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